

INFLUENCE OF RESIDUAL THERMAL STRESSES  
ON THE STRAIN SENSITIVITY OF THICK  
 $\text{Sn}_{0.9}\text{Sb}_{0.1}\text{O}_2$ -BASED FILMS

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S u m m a r y

The influence of residual thermal stresses resulting from the mismatch between the thermal expansion coefficients of the film and the substrate on the strain sensitivity of thick resistive  $\text{Sn}_{0.9}\text{Sb}_{0.1}\text{O}_2$ -based films has been studied. It has been found that the value of the strain sensitivity factor measured by the three-point bending method depends on the sign of residual stresses at the film—substrate interface. This phenomenon can be explained by a significant influence exerted by the processes of charge path reorganization on the variation of electrical resistance during deformation.